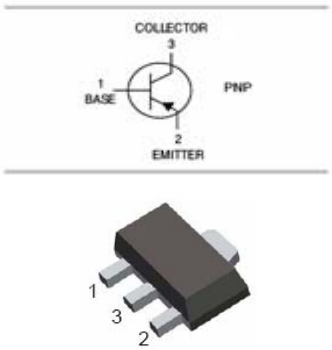
PNP Epitaxial Planar Silicon Transistors 2SB1119

FEATURES

- Very small size making it easy to provide High-density,small-size hybrid IC’s.

Lead-free



SOT-89

ORDERING INFORMATION

Type No.	Marking	Package Code
2SB1119	BB	SOT-89

MAXIMUM RATING @ Ta=25℃ unless otherwise specified

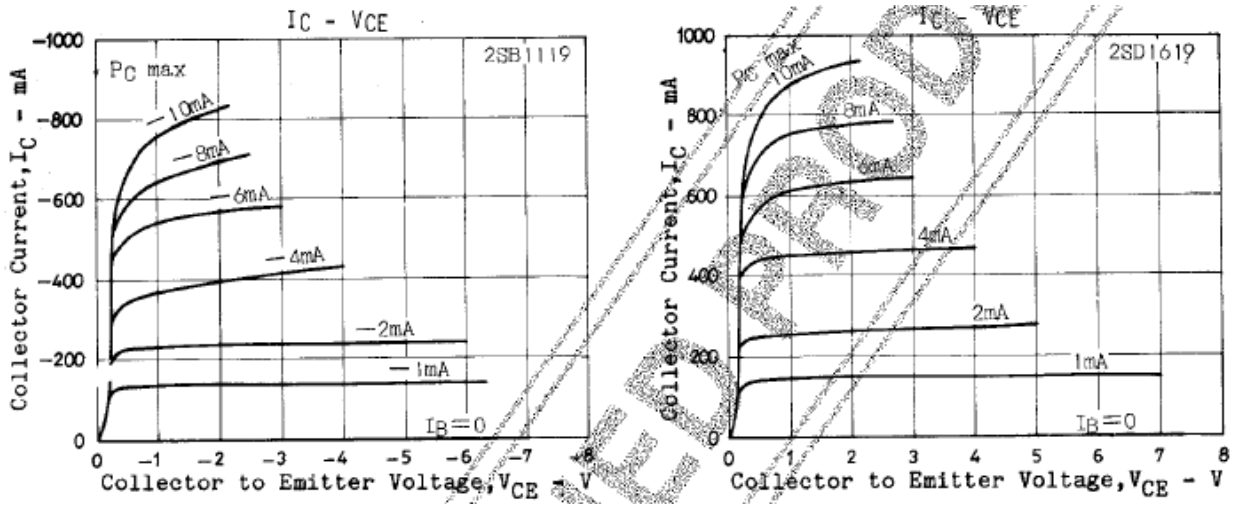
Symbol	**Parameter**	**Value**	**Unit**
V_{CBO}	Collector-Base Voltage	-25	V
V_{CEO}	Collector-Emitter Voltage	-25	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current –DC -Pulse	-1 -2	mA
P_C	Collector Dissipation	500	mW
T_j,T_{stg}	Junction and Storage Temperature	-55 to+150	℃

PNP Epitaxial Planar Silicon Transistors 2SB1119

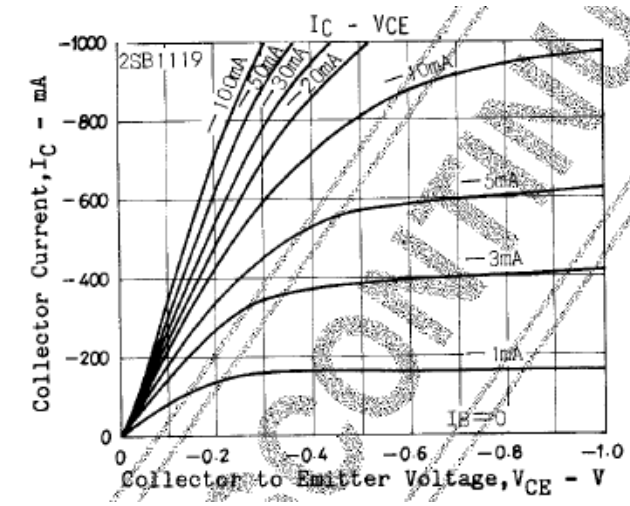
ELECTRICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

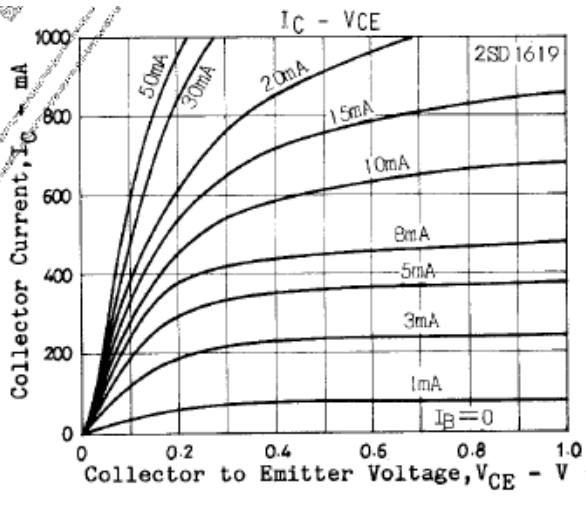
Parameter	Symbol	Test conditions	MIN		MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=-10μA I_E=0	-25			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-1mA I_B=0	-25			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-10μA I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-20V I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-0.1	μA
DC current gain	h_F	V_{CE}=-2V I_C=-50mA V_{CE}=-2V I_C=-1A	100 40		560	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA I_B=-50mA		-0.1	-0.3	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=-500mA I_B=-50mA		-0.85	-1.2	V
Transition frequency	f_T	V_{CE}=-10V,I_C=-50mA,		180		MHz
Output Capacitance	C_{obo}	V_{CB}=-10V f=1.0MHz I_E=0		15		pF

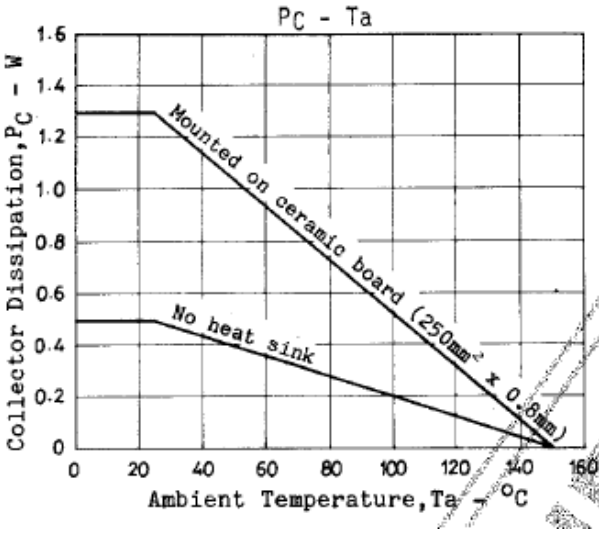
TYPICAL CHARACTERISTICS @ Ta=25℃ unless otherwise specified

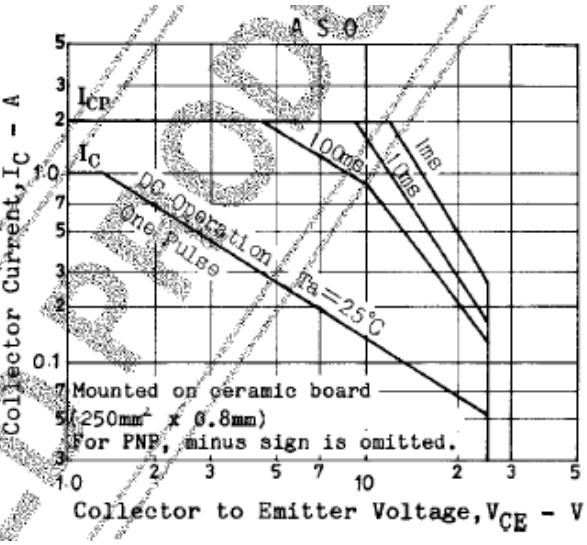


PNP Epitaxial Planar Silicon Transistors 2SB1119





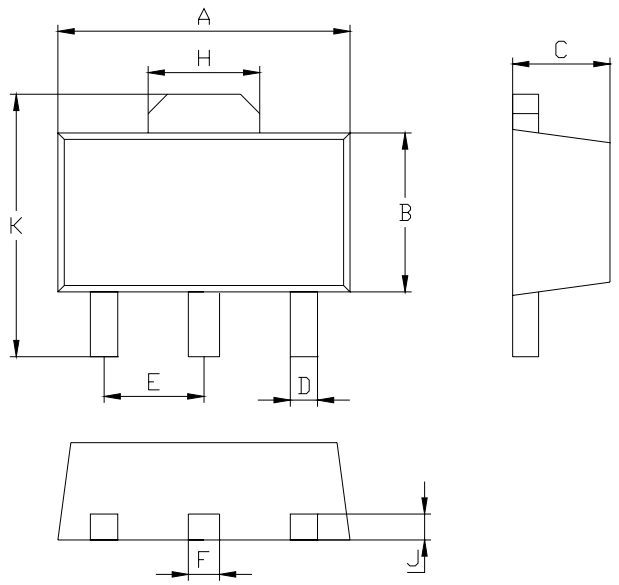




PNP Epitaxial Planar Silicon Transistors 2SB1119

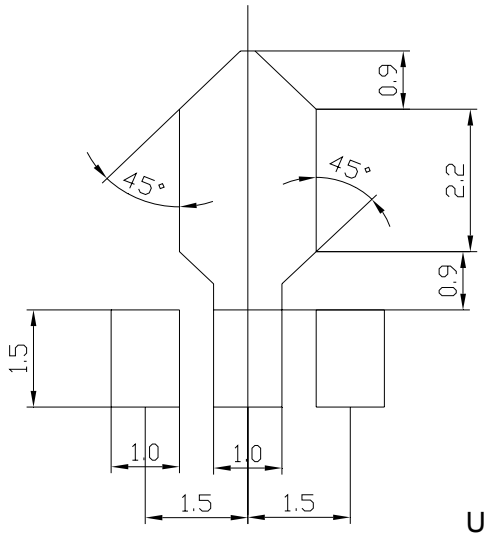
PACKAGE OUTLINE

Plastic surface mounted package SOT-89



SOT-89		
Dim	Min	Max
A	4.5	4.7
B	2.3	2.7
C	1.5Typical	
D	0.35	0.55
E	1.4	1.6
F	0.4	0.6
H	1.55	1.75
J	0.4Typical	
K	4.15	4.25
All Dimensions in mm		

SOLDERING FOOTPRINT



Unit:mm

PACKAGE INFORMATION

Device	Package	Shipping
2SB1119	SOT-89	1000/Tape&Reel